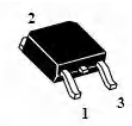
V_{DSS}	500 V
I_D	5 A
$R_{DS(ON)}$	1.3 Ω

FEATURES

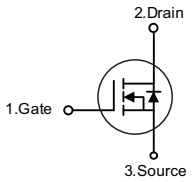
$R_{DS(ON)}$typ 1.3Ω@ V_{GS} =10V
Fast Switching Capability
Avalanche Energy Specified
Improved dv/dt Capability, High Ruggedness

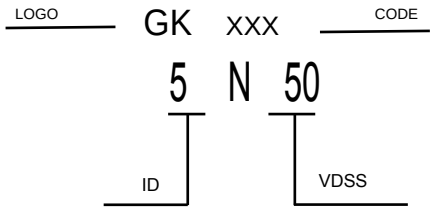


GK XXX
5N50

APPLICATION

High frequency switching mode power supply
Electronic ballast
LED power supply





MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	5	A
	Pulsed (Note 2)	I_{DM}	20	A
Avalanche Current (Note 2)		I_{AR}	5	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	300	mJ
	Repetitive (Note 2)	E_{AR}	7.3	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		P_D	125	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55~+150	°C

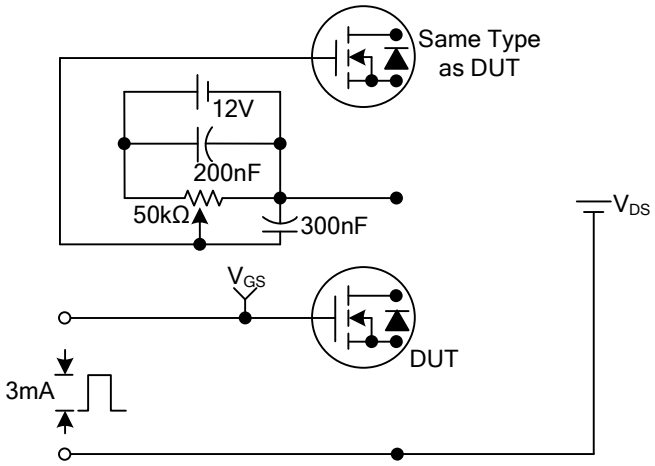
Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 21.5mH, I_{AS} = 5A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤5A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C, unless otherwise specified)

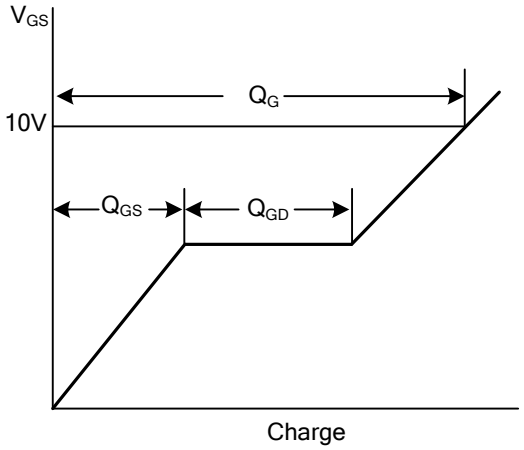
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	500			V
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	Reference to 25°C, I_D=250μA		0.5		V/°C
Drain-Source Leakage Current		I_{DSS}	V_{DS}=500V, V_{GS}=0V			1	μA
			V_{DS}=400V, T_C=125°C			10	
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=30V, V_{DS}=0V			100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=2.5A		1.3	1.55	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		480	625	pF
Output Capacitance		C_{OSS}			80	105	pF
Reverse Transfer Capacitance		C_{RSS}			15	20	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DS}=400V, I_D=5A (Note 1, 2)		18	24	nC
Gate to Source Charge		Q_{GS}			2.2		nC
Gate to Drain Charge		Q_{GD}			9.7		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=250V, I_D=5A, R_G=25Ω (Note 1, 2)		12	35	ns
Rise Time		t_R			46	100	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			50	110	ns
Fall-Time		t_F			48	105	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				5	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				20	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=5A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_S=5A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		83		ns
Reverse Recovery Charge		Q_{RR}			0.25		uC

Note: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

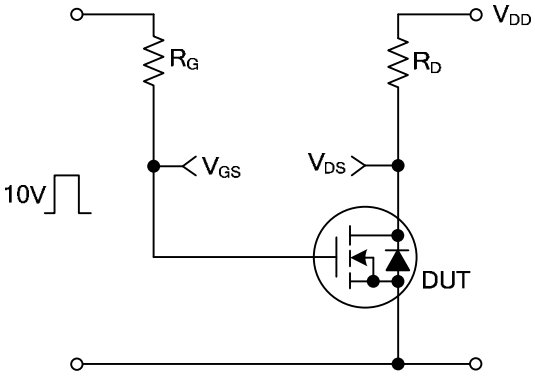
Test Circuits



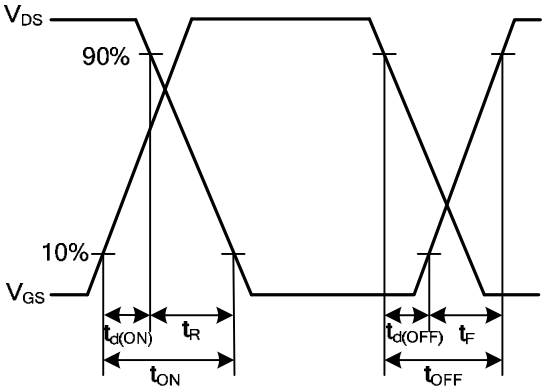
Gate Charge Test Circuit



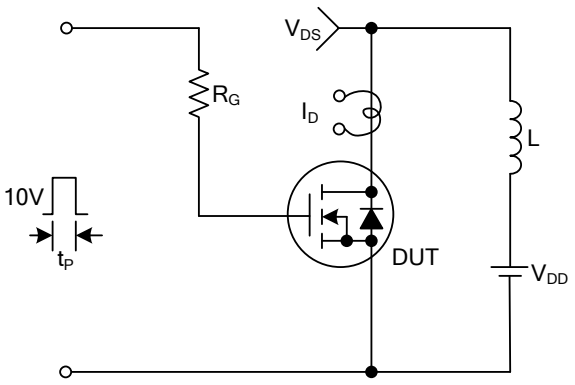
Gate Charge Waveforms



Resistive Switching Test Circuit

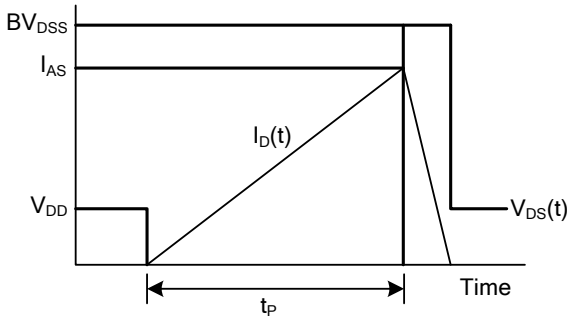


Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit

$$E_{AS}=\frac{1}{2}LI_{AS}^{2}\frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

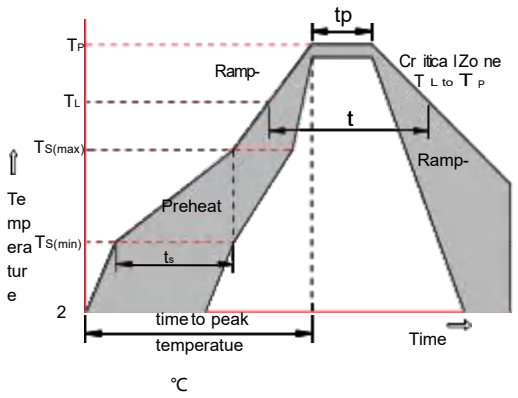


Unclamped Inductive Switching Waveforms

Soldering parameters

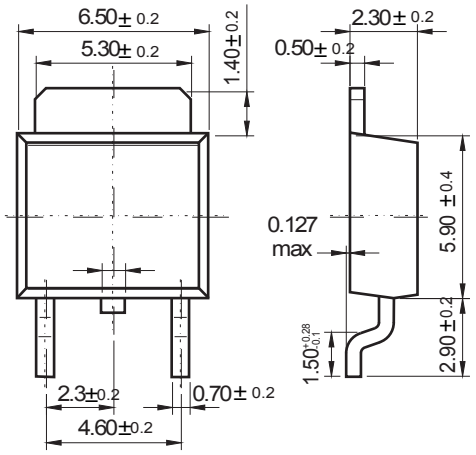
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition

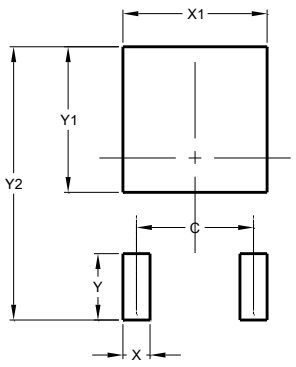


Package Dimensions & Suggested Pad Layout

TO-252



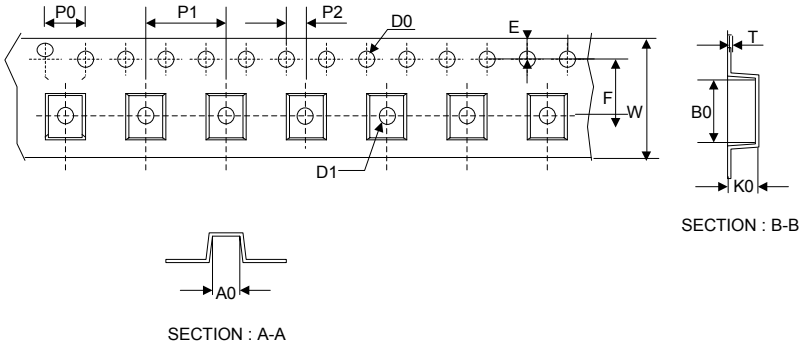
Dimensions in inches and (millimeters)



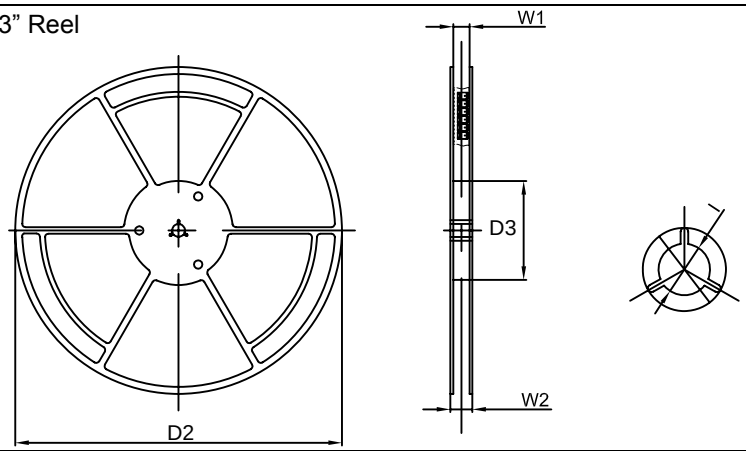
Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

Tape & rell specification

Tape



13” Reel



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.15
D1	1.55±0.20
E	1.75±0.20
F	7.50±0.20
W	16.00±0.20
A0	7.10±0.20
B0	10.50±0.20
K0	2.70±0.20
T	0.30±0.10
D2	330.0±5.0
D3	100.0±4.0
W1	20.0±5.0
W2	25.0±5.0
I	13.0±2.0

Quantity: 2500PCS

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.